

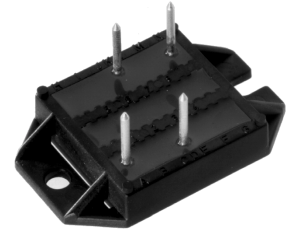
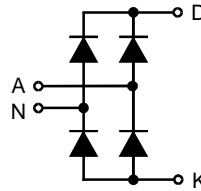
ECO-PAC™

Single Phase Rectifier Bridge

with Fast Recovery Epitaxial Diodes (FRED)

$I_{dAV} = 32 \text{ A}$
 $V_{RRM} = 1200 \text{ V}$
 $t_{rr} = 40 \text{ ns}$

| V_{RSM} | V_{RRM} | Typ |
|-----------|-----------|--------------|
| V | V | |
| 1200 | 1200 | VBE 26-12NO7 |



| Symbol | Conditions | Maximum Ratings | |
|-----------------|---|--------------------------|---------------------|
| I_{dAV} ① | $T_C = 85^\circ\text{C}$, module | 32 | A |
| | | 90 | A |
| I_{FSM} | $T_{VJ} = 45^\circ\text{C}$ $V_R = 0$ | t = 10 ms (50 Hz), sine | 90 A |
| | | t = 8.3 ms (60 Hz), sine | 100 A |
| | $T_{VJ} = T_{VJM}$ $V_R = 0$ | t = 10 ms (50 Hz), sine | 75 A |
| | | t = 8.3 ms (60 Hz), sine | 85 A |
| I^2t | $T_{VJ} = 45^\circ\text{C}$ $V_R = 0$ | t = 10 ms (50 Hz), sine | 40 A ² s |
| | | t = 8.3 ms (60 Hz), sine | 40 A ² s |
| | $T_{VJ} = T_{VJM}$ $V_R = 0$ | t = 10 ms (50 Hz), sine | 30 A ² s |
| | | t = 8.3 ms (60 Hz), sine | 30 A ² s |
| T_{VJ} | | -40...+150 | °C |
| T_{VJM} | | 150 | °C |
| T_{stg} | | -40...+125 | °C |
| V_{ISOL} | 50/60 Hz, RMS t = 1 min $I_{ISOL} \leq 1 \text{ mA}$ t = 1 s | 3000 | V~ |
| | | 3600 | V~ |
| M_d Weight | Mounting torque (M4) typ. | 1.5-2/14-18 | Nm/lb.in. |
| | | 19 | g |

Features

- Package with DCB ceramic base plate in low profile
- Isolation voltage 3000 V~
- Planar passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering

Applications

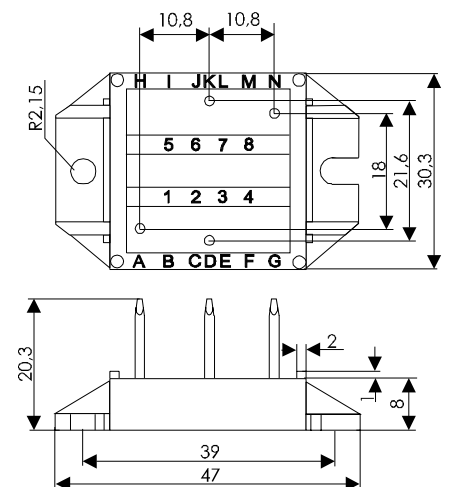
- Supplies for DC power equipment
- Input and output rectifiers for high frequency
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Space and weight savings
- Improved temperature and power cycling capability
- Small and light weight
- Low noise switching

| Symbol | Conditions | Characteristic Values | |
|------------|--|---|------------------|
| | | typ. | max. |
| I_R | $V_R = V_{RRM}$ $V_R = V_{RRM}$ | $T_{VJ} = 25^\circ\text{C}$ | 0.1 mA |
| | | $T_{VJ} = T_{VJM}$ | 0.5 mA |
| V_F | $I_F = 15 \text{ A}$ $T_{VJ} = 25^\circ\text{C}$ | | 2.73 V |
| V_{T0} | for power-loss calculations only | | 1.32 V |
| r_T | | | 30 mΩ |
| R_{thJC} | per diode; DC current | | 1.6 K/W |
| R_{thCH} | per diode, DC current, typ. | | 0.3 K/W |
| I_{RM} | $I_F = 25 \text{ A}$, -diF/dt = 100 A/μs $V_R = 100 \text{ V}$, L = 0.05 mH, $T_{VJ} = 100^\circ\text{C}$ | 5 | 9.7 A |
| | | $I_F = 1 \text{ A}$; -di/dt = 100 A/μs; $V_R = 30 \text{ V}$, $T_{VJ} = 25^\circ\text{C}$ | 40 |
| a | Max. allowable acceleration | 50 | m/s ² |
| d_s | creeping distance on surface | 11.2 | mm |
| d_A | creepage distance in air | 9.7 | mm |

Dimensions in mm (1 mm = 0.0394")



Data according to IEC 60747 refer to a single diode unless otherwise stated
 ① for resistive load at bridge output.

IXYS reserves the right to change limits, test conditions and dimensions.

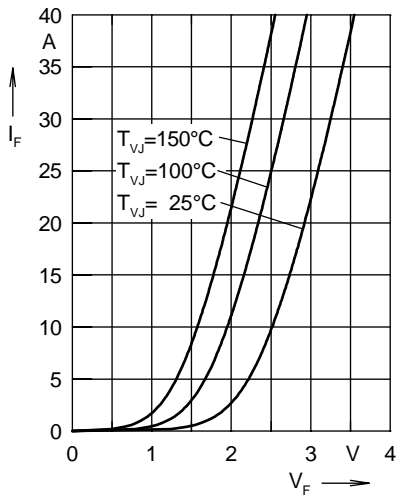


Fig. 1 Forward current I_F versus V_F

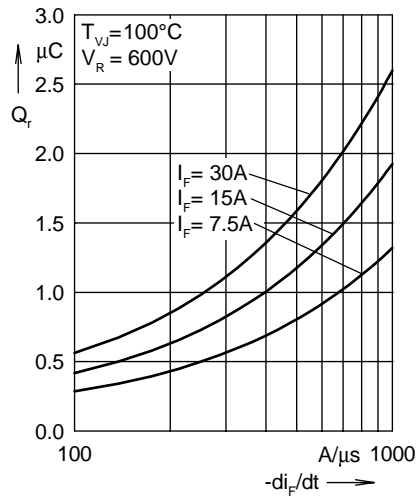


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

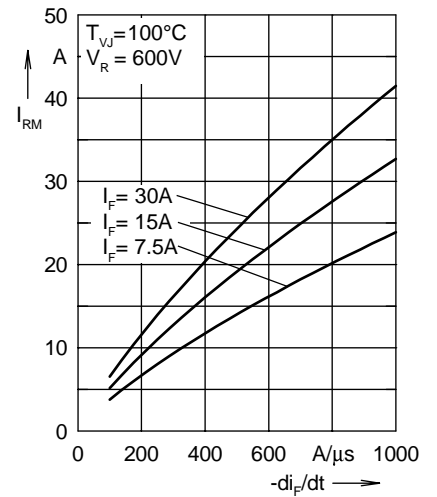


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

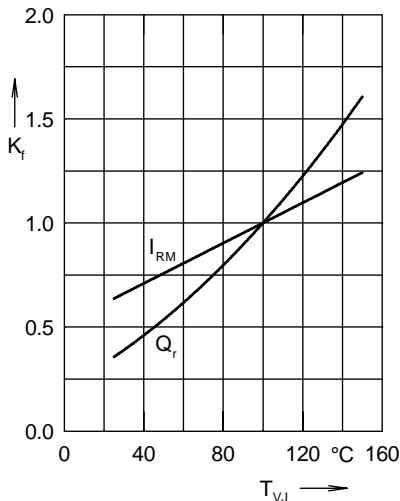


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

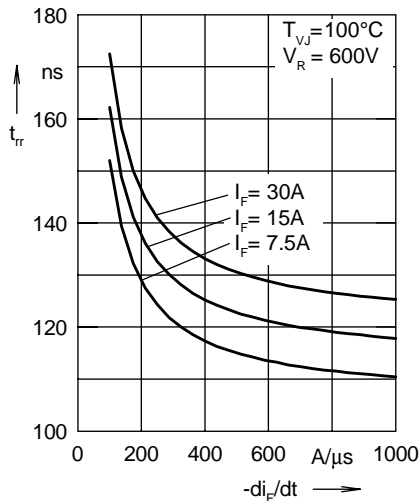


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

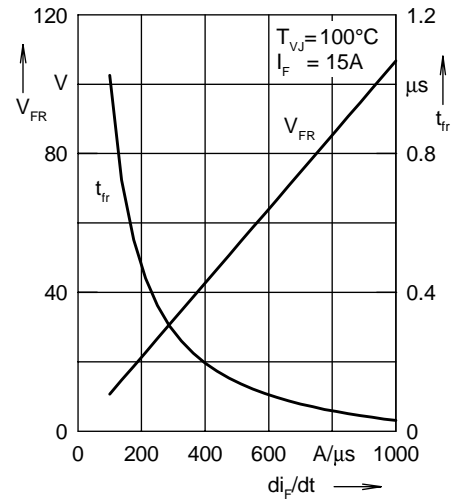


Fig. 6 Peak forward voltage V_{FR} and t_{rr} versus di_F/dt

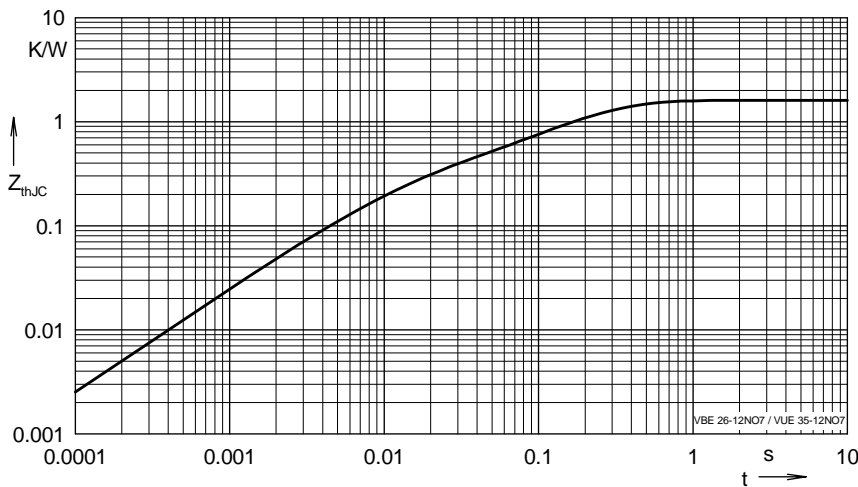


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

| i | R_{thi} (K/W) | t_i (s) |
|---|-----------------|-----------|
| 1 | 0.5464 | 0.0052 |
| 2 | 0.2104 | 0.0003 |
| 3 | 0.0432 | 0.0004 |
| 4 | 0.8 | 0.0092 |

NOTE: Fig. 2 to Fig. 6 shows typical values